

In the claims:

Following is a complete set of claims as amended with this Response.

1. (Original) A method comprising:  
  
applying plasma power to a plasma enhanced sequential chemical vapor  
deposition chamber;  
  
introducing a deposition gas after applying the plasma power;  
  
starting nitride deposition in the chamber to form a first portion of a layer on a  
substrate; and  
  
turning off the plasma power.
2. (Original)The method of Claim 1, further comprising:  
  
reapplying plasma power;  
  
reintroducing a deposition gas after reapplying the plasma power;  
  
starting nitride deposition in the chamber to form a second portion of the layer on  
the substrate after reapplying the plasma power; and  
  
turning off the plasma power.
3. (Original)The method of Claim 2, wherein introducing a deposition gas  
comprises introducing silane gas.
4. (Original)The method of Claim 2, wherein introducing silane gas  
comprises introducing silane gas at least 0.5 seconds after applying plasma power.
5. (Original)The method of Claim 2, wherein introducing silane gas  
comprises diverting silane gas from a pump to the deposition chamber.

6. (Original)The method of Claim 1, further comprising initiating set up gas flow and pressure in the chamber before applying the plasma power.

7. (Original)The method of Claim 6, wherein initiating set-up gas flow comprises flowing ammonia and nitrogen gases into the chamber.

8. (Currently Amended)The method of Claim 2 ~~Claim 1~~, further comprising pumping away residue gases after turning off the plasma power and before reapplying the plasma power.

9. (Currently Amended)The method of Claim 2 ~~Claim 1~~, further comprising moving a first nitride supply fixture to form the first portion of the layer away from the wafer and moving a second nitride supply fixture to form the second portion of the layer to the wafer after forming the first portion of the layer and before forming the second portion of the layer.

10. (Currently Amended)The method of Claim 2 ~~Claim 1~~, further comprising moving the wafer to another chemical vapor deposition position after forming the first portion of the layer and before forming the second portion of the layer.

11. (Original)The method of Claim 1, further comprising repeating turning on and off the nitride supply and the plasma power substantially simultaneously until a complete layer is formed.

12. (Currently Amended) An apparatus ~~A semiconductor device~~ having a layer formed in accordance with the method of Claim 1.

13. (Currently Amended)The apparatus ~~semiconductor device~~ of Claim 12 wherein the layer is a nitride etch stop layer.

14. (Currently Amended) The apparatus of Claim 12, wherein A  
~~semiconductor device comprising a layer formed by sequential chemical vapor~~  
~~deposition~~, the layer has ~~having~~ no intra-film interfaces corresponding to transitions of  
the sequential chemical vapor deposition formation.

15. (Currently Amended) The apparatus ~~semiconductor device~~ of Claim 14  
wherein the layer is a nitride etch stop layer.

16. (Currently Amended) The apparatus ~~semiconductor device~~ of Claim 14  
wherein the layer is a silicon nitride layer.

17. (Currently Amended) The apparatus ~~semiconductor device~~ of Claim 14  
wherein the layer is an insulating layer for a gate of a flash memory transistor.

18. (Currently Amended) The apparatus of Claim 12, further A ~~semiconductor~~  
~~device~~ comprising:

a drain area;

a source area; and

a gate layer coupled to the drain area and the source area;

wherein the layer overlies a sequential deposition nitride layer overlying the gate  
layer, the nitride layer having no intra-film interfaces corresponding to transitions of the  
sequential deposition.

19. (Canceled)

20. (Canceled)